

12.1 The number of dice per wafer is

$$N_{Dice} \approx \pi \left(\frac{D_w}{2L_c} - 1 \right)^2 = \pi \left(\frac{8 \cdot 25.4}{2L_c} - 1 \right)^2 = 561, 263, \text{ and } 167 \text{ dice.}$$

The active area d is close to 1 for a high-density chip. Thus, $d A D \approx 0.95 A 0.03 > 1$. Hence, we use Murphy-Moores model for the yield

$$Y = 0.5 \left[\frac{1 - e^{-dAD}}{dAD} \right]^2 + 0.5 e^{-\sqrt{dAD}}$$

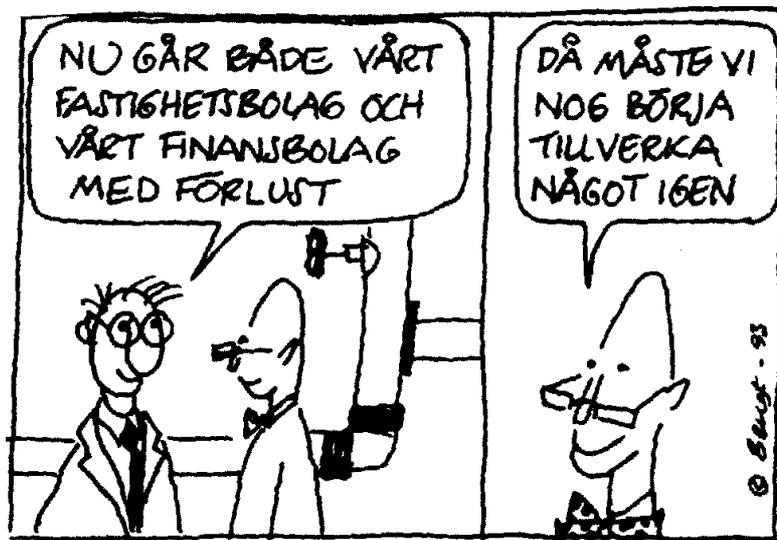
We have: $d A D = 1.425, 2.85, \text{ and } 4.275$. The yield is estimated to: 29.4%, 14.7%, and 9.0%. The cost is estimated to: $\$600 Y/N_{dice} = \$4.66, \$15.52, \text{ and } \39.92 per die. Further, costs for testing, bounding, and packaging are incurred. For a small die, the cost of the package may be dominant.

12.4 The excess junction temperature (above 25 °C) is: $T_j = 172 \cdot 0.4 = 69$ °C. The contribution from excess temperature, process spread, and reduced voltage is

$$\begin{aligned} \tau_{CL req} &= (1 + 3.75 \cdot 10^{-3} \cdot 69)(1 + 0.35)(1 + 0.3 \cdot 0.25) \tau_{CL design} = \\ &= 1.2588 \cdot 1.35 \cdot 1.075 \tau_{CL design} = 1.827 \tau_{CL design} \end{aligned}$$

$$f_{CL design} = 1.827 \cdot f_{CL req} = 1.827 \cdot 50 = 91.4 \text{ MHz}$$

Thus, the circuit should be designed with nominal parameter values to run with a clock frequency that exceeds the required frequency with 83%.



"Now when our real estate and finance branches are in the red we may have to start to manufacturing something"